MSKSEMI 美森科













ESD

TV

TSS

MOV

GDT

PIFD

2SC3356 XXX

Product specification

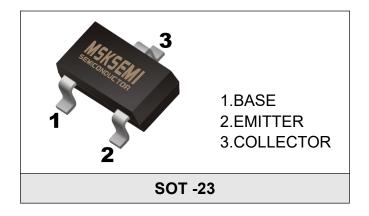




TRANSISTOR (NPN)

FEATURES

- Low Noise and High Gain
- High Power Gain



MARKING&CLASSIFICATION OF hfe(1)

RANGE	50 -100	80 -160	125 -250	
MARKING	R23	R24	R25	
Туре	2SC3356 R23	2SC3356 R24	2SC3356 R25	

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

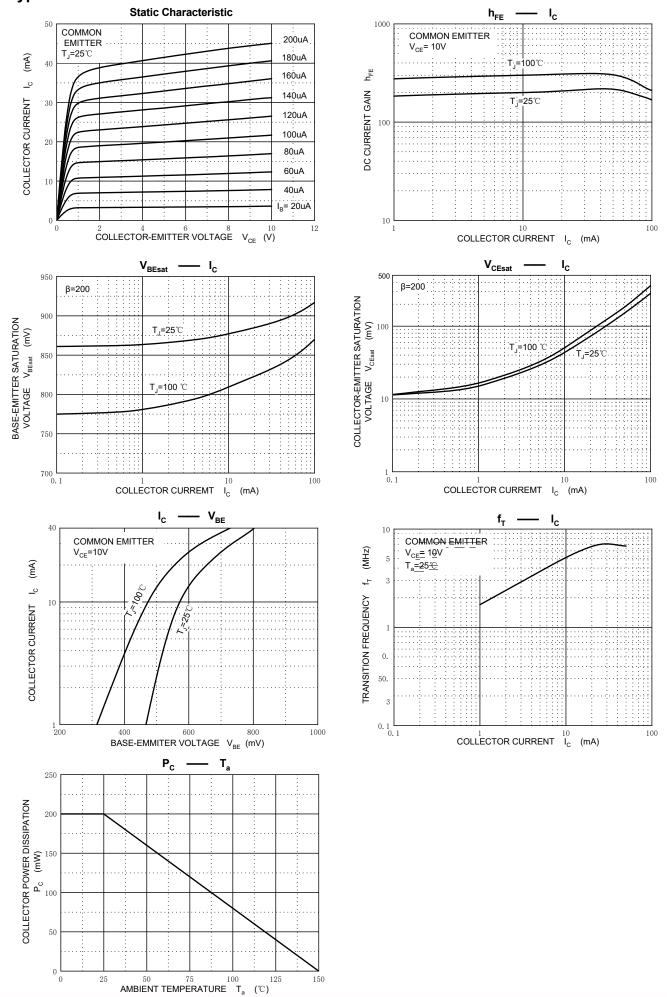
Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	20	V
Vceo	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	3	V
lc	Collector Current	100	mA
Pc	Collector Power Dissipation	200	mW
Roja	Thermal Resistance From Junction To Ambient	625	°C/W
T _j ,T _{stg}	Operation Junction and Storage Temperature Range	-55 ~ +125	℃

ELECTRICAL CHARACTERISTICS (Ta=25 $^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	20			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	12			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	l _E =100μA, I _C =0	3			V
Collector cut-off current	Ісво	V _{CB} =10V, I _E =0			1	uA
Emitter cut-off current	I _{EBO}	V _{EB} =1V, I _C =0			1	uA
DC current gain	h _{FE(1)}	V _{CE} =10V, I _C =20mA	50		250	
Collector-emitter saturation voltage	V _{CE(sat)}	lc=50mA, I _B =5mA			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	lc=50mA, I _B =5mA			1.15	V
Transition frequency	f⊤	V _{CE} =10V,I _C =20mA		7		GHz
Collector output capacitance	Cob	V _{CB} =10V, I _E =0, f=1MHz		0.8	1	pF
Noise Figure	N _F	V _{CB} =10V, I _C =7mA, f=1GHz		1.65	2	dB

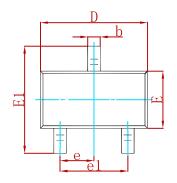


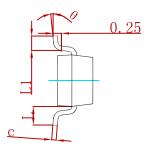
Typical Characteristics

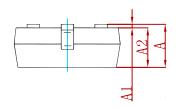




PACKAGE MECHANICAL DATA

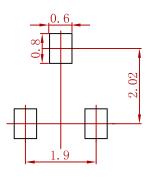






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SC3356 XXX	SOT-23	3000



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